

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1898	SERIAL NO. 09/633,556
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.	
				FILING DATE August 7, 2000	GROUP 2813

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U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
<i>[Handwritten signatures and initials in left margin]</i>	AA	5,032,545	07/91	Doan et al.			
	AB	5,436,481	07/95	Egawa et al.			
	AC	5,378,645	01/95	Inoue et al.			
	AD	5,258,333	11/93	Shappir et al.			
	AE	5,518,946	05/96	Kuroda			
	AF	5,445,999	08/95	Thakur et al.			
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	AH	5,663,077	09/97	Adachi et al.			
	AI	5,026,574	06/91	Economu et al.			
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	AK	5,612,558	11/95 3/1997	Harshfield			
	AL	5,719,083	06/95 2/1998	Komatsu			

Gurtej S. Sandhu
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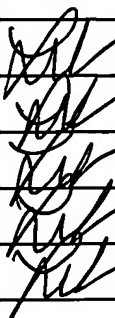

FOREIGN PATENT DOCUMENTS							
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						Yes	No
	AM	WO 96/39713	12/96	PCT			
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)		
AR		Wolf, S., "Silicon Processing for the VLSI Era", Lattice Press 1990, Vol. 2, pp. 212-213.
AS		Wolf, S., "Silicon Processing for the VLSI Era", Lattice Press 1990, Vol. 2, pp. 188-189, 194-195, 609-614.
AT		Ko, L. et al., "The Effect of Nitrogen Incorporation into the Gate Oxide By Using Shallow Implantation of Nitrogen and Drive-In Process", IEEE 1996, pp. 32-35.

EXAMINER <i>[Signature: Hanna Schultze]</i>	DATE CONSIDERED 6/5/02
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
<i>Handwritten:</i> Gurtej Sandhu	AA	5,760,475	06/98	Cronin			
	AB	5,834,372	11/98	Lee			
	AC	5,619,057	04/96 1997	Komatsu			
	AD	5,633,036	05/97	Seebauer et al.			
	AE	6,054,396	04/00	Doan			
	AF	6,174,821	01/01	Doan			
	AG	5,939,750	08/99	Early			
	AH	5,254,489	10/93	Nakata			
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	AR		Doyle, B. et al., "Simultaneous Growth of Different Thickness Gate Oxides in Silicon CMOS Processing", IEEE Vol. 16 (7), July 1995, pp. 301-302.				
	AS		Kuroi, T. et al., "The Effects of Nitrogen Implantation Into P+Poly-Silicon Gate on Gate Oxide Properties", 1994 Sympos. on VLSI Technology Digest of Technical Papers, IEEE 1994, pp. 107-108.				
	AT		Liu, C.T. et al., "Multiple Gate Oxide Thickness for 2GHz System-on-a-Chip Technologies" IEEE 1998, pp. 589-592.				
EXAMINER <i>Handwritten:</i> Laura Schillinger				DATE CONSIDERED <i>Handwritten:</i> 6/5/02			
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	AA	6,091,109	07/00	Hasegawa			
	AB	6,080,682	06/00	Ibok			
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MI22-1898SERIAL NO.
10/050,348LIST OF ART CITED BY APPLICANT
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EXAMINER

Haeena Schuff

DATE CONSIDERED

6/3/02

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